

Tentative Data Sheet 2L10ES

Active area: 10,0 x 10,0 mm²

Chip area: 12,2 x 12,2 mm²

Characteristics	Min.	Typ.	Max.	Unit
Position non-linearity		0,3	0,8	% (±)
Detector resistance	7	10	16	kΩ
Leakage current		100	500	nA
Noise current		1,3	2,5	pA/√Hz
Responsivity		3		A/W
Capacitance		90	110	pF
Rise time (10%-90%)		4	8	μs
Bias voltage (reverse)	5	15	30	V
Thermal drift		40	200	ppm/°C
Maximum ratings				
Reverse voltage			30	V
Operating temperature			70	°C
Storage temperature			100	°C

Test conditions: Room temperature 23 °C, bias voltage 15V, light source wavelength 940 nm. Position non-linearity and thermal drift are valid within 80 % of the detector length.

Package: 4-pin ceramic package, 25,0 x 25,0 mm², with protective window.